Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	41
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 25x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8al3168tcy

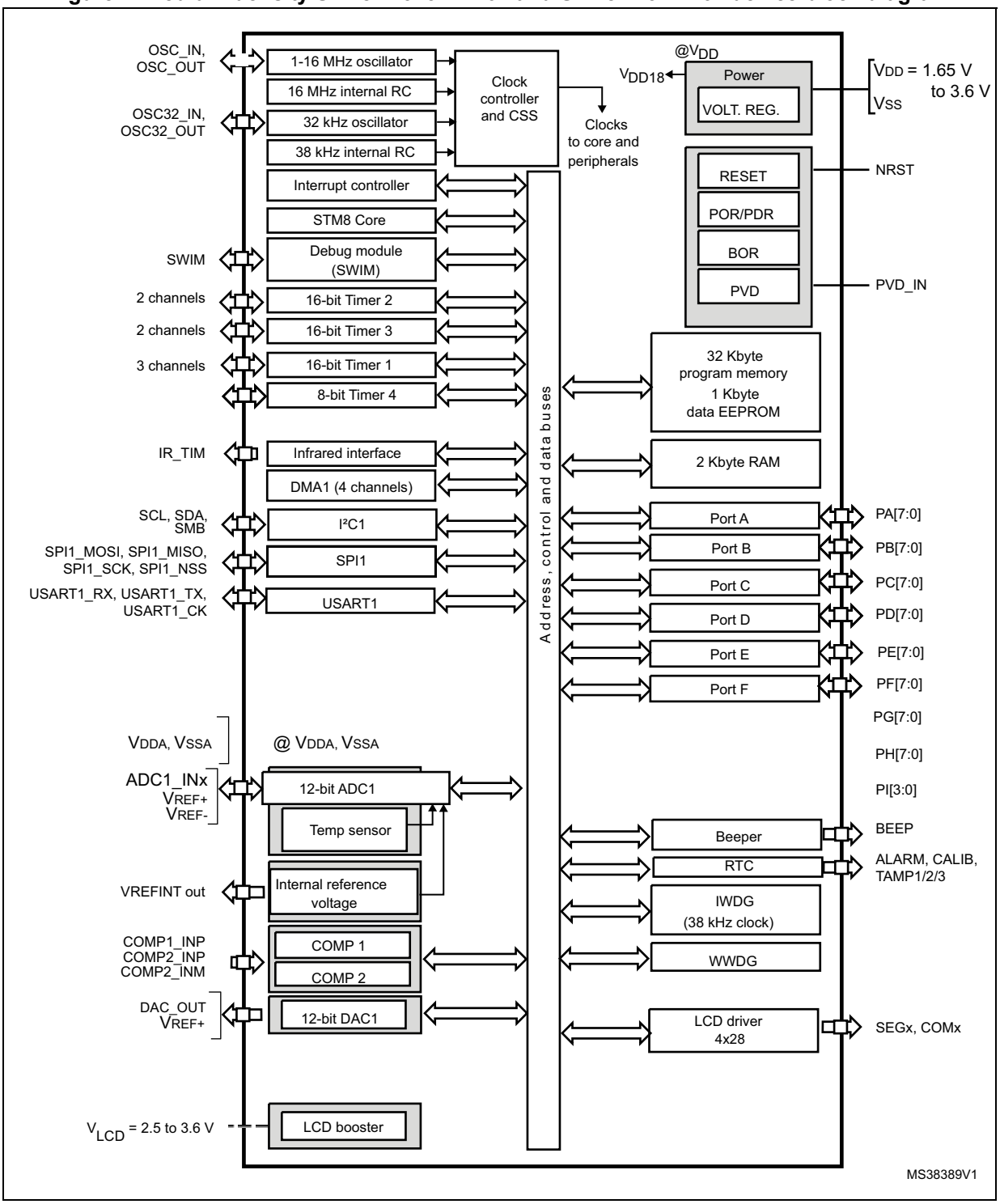
- Development support
  - Fast on-chip programming and non intrusive debugging with SWIM
  - Bootloader using USART
- 96-bit unique ID

Table 1. Device summary

Reference	Part number
STM8AL313x/4x/6x (without LCD)	STM8AL3136, STM8AL3138, STM8AL3146, STM8AL3148, STM8AL3166, STM8AL3168
STM8AL3L4x/6x (with LCD)	STM8AL3L46, STM8AL3L48, STM8AL3L66, STM8AL3L68

3 Functional overview

Figure 1. Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x device block diagram



1. **Legend**: ADC (Analog-to-digital converter), BOR (Brownout reset), DMA (Direct memory access), DAC (Digital-to-analog converter), I²C (Inter-integrated circuit multimaster interface), IWDG (Independent watchdog), LCD (Liquid crystal display), POR/PDR (Power on reset / power down reset), RTC (Real-time clock), SPI (Serial peripheral interface), SWIM (Single wire interface module), USART (Universal synchronous asynchronous receiver transmitter), WWDG (Window watchdog).

3.13 Timers

The medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x devices contain one advanced control timer (TIM1), two 16-bit general purpose timers (TIM2 and TIM3) and one 8-bit basic timer (TIM4).

All the timers can be served by DMA1.

Table 3 compares the features of the advanced control, general-purpose and basic timers.

Table 3. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA1 request generation	Capture/compare channels	Complementary outputs
TIM1	16-bit	up/down	Any integer from 1 to 65536	Yes	3 + 1	3
TIM2			Any power of 2 from 1 to 128		2	None
TIM3						
TIM4	8-bit	up	Any power of 2 from 1 to 32768		0	

3.13.1 TIM1 - 16-bit advanced control timer

This is a high-end timer designed for a wide range of control applications. With its complementary outputs, dead-time control and center-aligned PWM capability, the field of applications is extended to motor control, lighting and half-bridge driver.

- 16-bit up, down and up/down auto reload counter with 16-bit prescaler
- Three independent capture/compare channels (CAPCOM) configurable as input capture, output compare, PWM generation (edge and center aligned mode) and single pulse mode output.
- One additional capture/compare channel which is not connected to an external I/O
- Synchronization module to control the timer with external signals
- Break input to force timer outputs into a defined state
- Three complementary outputs with adjustable dead time
- Encoder mode
- Interrupt capability on various events (capture, compare, overflow, break, trigger)

3.13.2 16-bit general purpose timers

- 16-bit auto reload (AR) up/down-counter
- 7-bit prescaler adjustable to fixed power of 2 ratios (1…128)
- Two individually configurable capture/compare channels
- PWM mode
- Interrupt capability on various events (capture, compare, overflow, break, trigger)
- Synchronization with other timers or external signals (external clock, reset, trigger and enable)

Table 5. Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x pin description (continued)

Pin number			Pin name	Type	I/O level	Input			Output			Main function (after reset)	Default alternate function
LQFP48	VFQFPN32	LQFP32				floating	wpu	Ext. interrupt	High sink/source	OD	PP		
38	26	26	PC1(5)/I2C1_SCL	I/O	FT	X	-	X	-	T(7)		Port C1	I2C1 clock
41	27	27	PC2/USART1_RX/ LCD_SEG22/ADC1_IN6/ COMP1_INP/VREFINT	I/O	TT(3)	X	X	X	HS	X	X	Port C2	USART1 receive / LCD segment 22 / ADC1_IN6 / Comparator 1 positive input / Internal voltage reference output
42	28	28	PC3/USART1_TX/ LCD_SEG23(2)/ ADC1_IN5/COMP1_INP/ COMP2_INM	I/O	TT(3)	X	X	X	HS	X	X	Port C3	USART1 transmit / LCD segment 23 / ADC1_IN5 / Comparator 1 positive input / Comparator 2 negative input
43	29	29	PC4/USART1_CK/ I2C1_SMB/CCO/ LCD_SEG24(2)/ ADC1_IN4/COMP2_INM/ COMP1_INP	I/O	TT(3)	X	X	X	HS	X	X	Port C4	USART1 synchronous clock / I2C1_SMB / Configurable clock output / LCD segment 24 / ADC1_IN4 / Comparator 2 negative input / Comparator 1 positive input
44	30	30	PC5/OSC32_IN /*[SPI1_NSS]*(4)/ *[USART1_TX]*(4)	I/O	-	X	X	X	HS	X	X	Port C5	LSE oscillator input / *[SPI1 master/slave select] / [USART1 transmit]*
45	31	31	PC6/OSC32_OUT/ *[SPI1_SCK]*(4)/ *[USART1_RX]*(4)	I/O	-	X	X	X	HS	X	X	Port C6	LSE oscillator output / *[SPI1 clock] / [USART1 receive]*
46	-	-	PC7/LCD_SEG25(2)/ ADC1_IN3/COMP2_INM/ COMP1_INP	I/O	TT(3)	X	X	X	HS	X	X	Port C7	LCD segment 25 /ADC1_IN3/ Comparator negative input / Comparator 1 positive input

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5055 to 0x00 506F	Reserved area (27 bytes)			
0x00 5070	DMA1	DMA1_GCSR	DMA1 global configuration & status register	0xFC
0x00 5071		DMA1_GIR1	DMA1 global interrupt register 1	0x00
0x00 5072 to 0x00 5074		Reserved area (3 bytes)		
0x00 5075		DMA1_C0CR	DMA1 channel 0 configuration register	0x00
0x00 5076		DMA1_C0SPR	DMA1 channel 0 status & priority register	0x00
0x00 5077		DMA1_C0NDTR	DMA1 number of data to transfer register (channel 0)	0x00
0x00 5078		DMA1_C0PARH	DMA1 peripheral address high register (channel 0)	0x52
0x00 5079		DMA1_C0PARL	DMA1 peripheral address low register (channel 0)	0x00
0x00 507A		Reserved area (1 byte)		
0x00 507B		DMA1_C0M0ARH	DMA1 memory 0 address high register (channel 0)	0x00
0x00 507C		DMA1_C0M0ARL	DMA1 memory 0 address low register (channel 0)	0x00
0x00 507D to 0x00 507E	Reserved area (2 bytes)			

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 50A9 to 0x00 50AF	Reserved area (7 bytes)			
0x00 50B0	RST	RST_CR	Reset control register	0x00
0x00 50B1		RST_SR	Reset status register	0x01
0x00 50B2	PWR	PWR_CSR1	Power control and status register 1	0x00
0x00 50B3		PWR_CSR2	Power control and status register 2	0x00
0x00 50B4 to 0x00 50BF	Reserved area (12 bytes)			
0x00 50C0	CLK	CLK_DIVR	Clock master divider register	0x03
0x00 50C1		CLK_CRTCR	Clock RTC register	0x00
0x00 50C2		CLK_ICKR	Internal clock control register	0x11
0x00 50C3		CLK_PCKENR1	Peripheral clock gating register 1	0x00
0x00 50C4		CLK_PCKENR2	Peripheral clock gating register 2	0x80
0x00 50C5		CLK_CCOR	Configurable clock control register	0x00
0x00 50C6		CLK_ECKR	External clock control register	0x00
0x00 50C7		CLK_SCSR	System clock status register	0x01
0x00 50C8		CLK_SWR	System clock switch register	0x01
0x00 50C9		CLK_SWCR	Clock switch control register	0bxxxx0000
0x00 50CA		CLK_CSSR	Clock security system register	0x00
0x00 50CB		CLK_CBEEPR	Clock BEEP register	0x00
0x00 50CC		CLK_HSICALR	HSI calibration register	0xxx
0x00 50CD		CLK_HSITRIMR	HSI clock calibration trimming register	0x00
0x00 50CE		CLK_HSIUNLCKR	HSI unlock register	0x00
0x00 50CF		CLK_REGCSR	Main regulator control status register	0bxx11100x
0x00 50D0 to 0x00 50D2	Reserved area (3 bytes)			
0x00 50D3	WWDG	WWDG_CR	WWDG control register	0x7F
0x00 50D4		WWDG_WR	WWDR window register	0x7F
0x00 50D5 to 00 50DF	Reserved area (11 bytes)			
0x00 50E0	IWDG	IWDG_KR	IWDG key register	0xXX
0x00 50E1		IWDG_PR	IWDG prescaler register	0x00
0x00 50E2		IWDG_RLR	IWDG reload register	0xFF

Table 13. Option byte description

Option byte no.	Option description
OPT0	**ROP[7:0]** Memory readout protection (ROP) 0xAA: Disable readout protection (write access via SWIM protocol) Refer to Readout protection section in STM8L05xx, STM8L15xx, STM8L162x, STM8AL31xx, STM8AL3Lxx, STM8AL31Exx and STM8AL3LExx MCU families reference manual (RM0031).
OPT1	**UBC[7:0]** Size of the user boot code area 0x00: No UBC 0x01: the UBC contains only the interrupt vectors. 0x02: Page 0 and 1 reserved for the UBC and read/write protected. Page 0 contains only the interrupt vectors. 0x03: Page 0 to 2 reserved for UBC, memory write-protected. 0xFF: Page 0 to 254 reserved for the UBC, memory write-protected. Refer to User boot code section in STM8L05xx, STM8L15xx, STM8L162x, STM8AL31xx, STM8AL3Lxx, STM8AL31Exx and STM8AL3LExx MCU families reference manual (RM0031).
OPT2	Reserved
OPT3	**IWDG_HW:** Independent watchdog 0: Independent watchdog activated by software 1: Independent watchdog activated by hardware
	IWDG_HALT: Independent watchdog off in Halt/Active-halt 0: Independent watchdog continues running in Halt/Active-halt mode 1: Independent watchdog stopped in Halt/Active-halt mode
	WWDG_HW: Window watchdog 0: Window watchdog activated by software 1: Window watchdog activated by hardware
	WWDG_HALT: Window window watchdog reset on Halt/Active-halt 0: Window watchdog stopped in Halt mode 1: Window watchdog generates a reset when MCU enters Halt mode
OPT4	**HSECNT**: Number of HSE oscillator stabilization clock cycles 0x00 - 1 clock cycle 0x01 - 16 clock cycles 0x10 - 512 clock cycles 0x11 - 4096 clock cycles
	LSECNT: Number of LSE oscillator stabilization clock cycles 0x00 - 1 clock cycle 0x01 - 16 clock cycles 0x10 - 512 clock cycles 0x11 - 4096 clock cycles Refer to *Table 33: LSE oscillator characteristics*

9 Electrical parameters

9.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

9.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = -40 °C, T_A = 25 °C, and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production.

9.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3 V. They are given only as design guidelines and are not tested.

Typical ADC and DAC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range.

9.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

9.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

Figure 10. Pin loading conditions

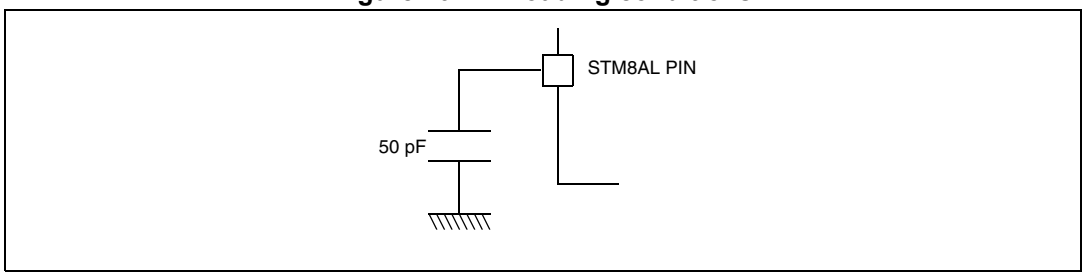


Table 16. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power line (source)	80	mA
I_{VSS}	Total current out of V_{SS} ground line (sink)	80	
I_{IO}	Output current sunk by IR_TIM pin (with high sink LED driver capability)	80	
	Output current sunk by any other I/O and control pin	25	
	Output current sourced by any I/Os and control pin	- 25	
$I_{INJ(PIN)}$	Injected current on true open-drain pins (PC0 and PC1)(1)	- 5/+0	
	Injected current on five-volt tolerant (FT) pins (PA7 and PE0)(1)	- 5/+0	
	Injected current on 3.6 V tolerant (TT) pins(1)	- 5/+0	
	Injected current on any other pin(2)	- 5/+5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(3)	± 25	

1. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15* for maximum allowed input voltage values.
2. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15* for maximum allowed input voltage values.
3. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 17. Thermal characteristics

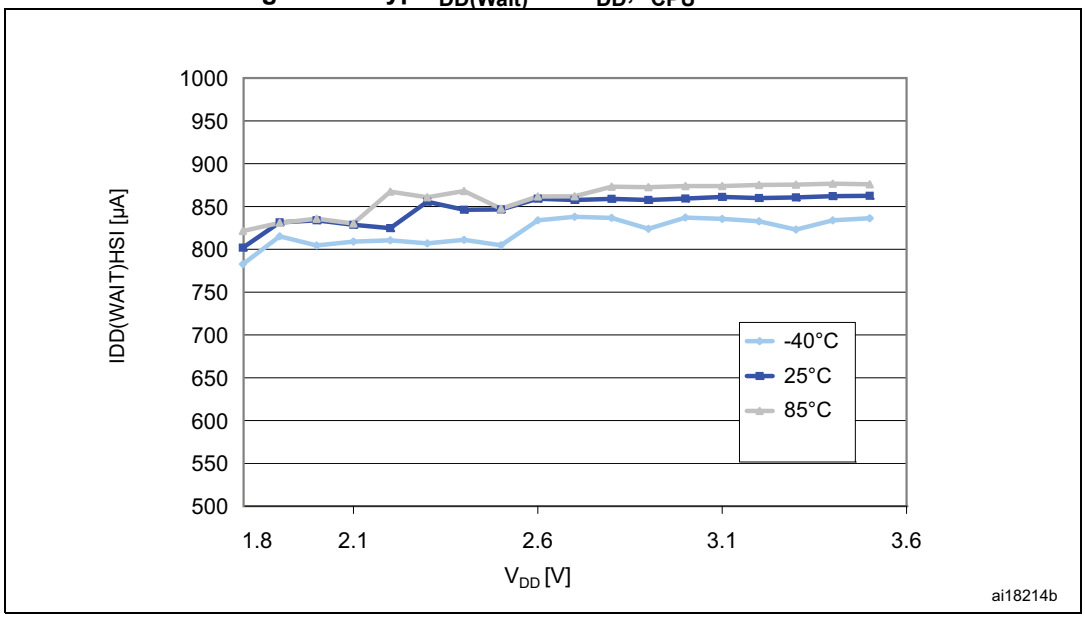
Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	° C
T_J	Maximum junction temperature	150	

Table 18. Operating lifetime (OLF)(1)

Symbol	Ratings	Value	Unit
OLF	Conforming to AEC-Q100	-40 to 125 °C	Grade 1

1. For detailed mission profile analysis, please contact the local ST Sales Office.

Figure 14. Typ. $I_{DD(Wait)}$ vs. V_{DD}, f_{CPU} = 16 MHz (1)



1. Typical current consumption measured with code executed from Flash memory

Table 23. Total current consumption and timing in low-power run mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions(1)			Typ	Max	Unit
$I_{DD(LPR)}$	Supply current in Low power run mode	LSI RC osc. (at 38 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	5.10	5.40(2)	µA
				T_A = 85 °C	6.80	11(3)	
				T_A = 125 °C	13.40	20(3)	
		LSE (4) external clock (32.768 kHz)	all peripherals OFF	T_A = -40 °C to 25 °C	5.25	5.60(2)	
				T_A = 85 °C	5.85	6.30(2)	
				T_A = 125 °C	9.85	12.00(2)	

1. No floating I/Os.
2. Guaranteed by characterization results.
3. Tested at 85°C for temperature range A or 125°C for temperature range C.
4. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ LSE}$) must be added. Refer to *Table 33*.

Table 29. Current consumption under external reset

Symbol	Parameter	Conditions		Typ	Unit
$I_{DD(RST)}$	Supply current under external reset (1)	All pins are externally tied to V_{DD}	V_{DD} = 1.8 V	48	µA
			V_{DD} = 3 V	76	
			V_{DD} = 3.6 V	91	

1. All pins except PA0, PB0 and PB4 are floating under reset. PA0, PB0 and PB4 are configured with pull-up under reset.

9.3.4 Clock and timing characteristics

HSE external clock (HSEBYP = 1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 30. HSE external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External clock source frequency	-	1(1)	-	16(1)	MHz
V_{HSEH}	OSC_IN input pin high level voltage		0.7 x V_{DD}	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	0.3 x V_{DD}	
$C_{in(HSE)}$	OSC_IN input capacitance	-	-	2.6	-	pF
I_{LEAK_HSE}	OSC_IN input leakage current	$V_{SS} < V_{IN} < V_{DD}$	-	-	±500	nA

1. Guaranteed by design.

LSE external clock (LSEBYP=1 in CLK_ECKCR)

Subject to general operating conditions for V_{DD} and T_A.

Table 31. LSE external clock characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSE_ext}	External clock source frequency	-	32.768	-	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	0.7 x V_{DD}(1)	-	V_{DD}(1)	V
V_{LSEL}	OSC32_IN input pin low level voltage	V_{SS}(1)	-	0.3 x V_{DD}(1)	
$C_{in(LSE)}$	OSC32_IN input capacitance	-	0.6	-	pF
I_{LEAK_LSE}	OSC32_IN input leakage current	-		±500	nA

1. Guaranteed by characterization results.

HSE crystal/ceramic resonator oscillator

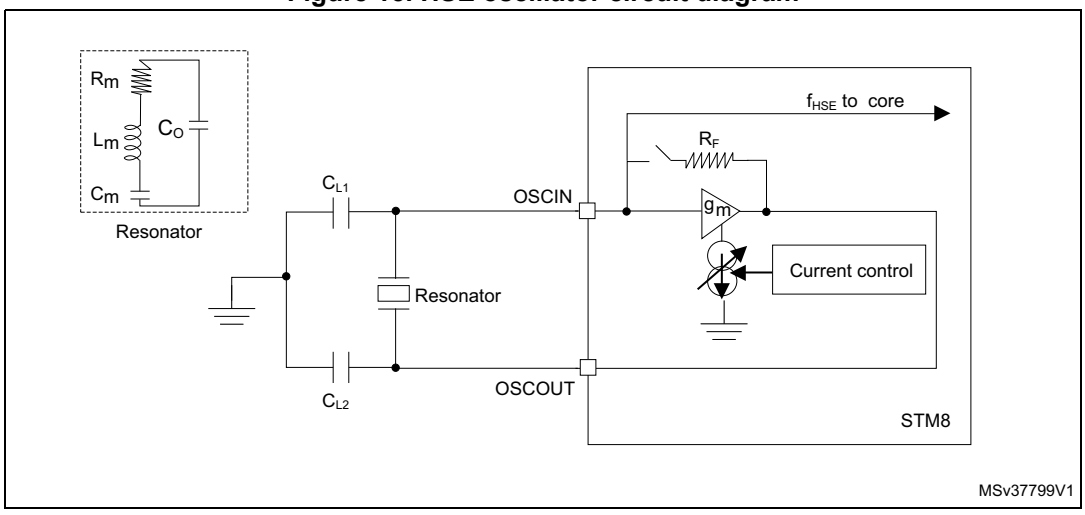
The HSE clock can be supplied with a 1 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 32. HSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE}	High speed external oscillator frequency	-	1	-	16	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
$C^{(1)}$	Recommended load capacitance $^{(2)}$	-	-	20	-	pF
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF, f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)$^{(3)}$	mA
		C = 10 pF, f_{OSC} =16 MHz	-	-	2.5 (startup) 0.46 (stabilized)$^{(3)}$	
g_m	Oscillator transconductance	-	3.5$^{(3)}$	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	1	-	ms

1. $C=C_{L1}=C_{L2}$ is approximately equivalent to 2 x crystal C_{LOAD}.
2. The oscillator selection can be optimized in terms of supply current using a high quality resonator with small R_m value. Refer to crystal manufacturer for more details
3. Guaranteed by design.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 16 MHz oscillation. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Figure 15. HSE oscillator circuit diagram



HSE oscillator critical g_m formula

$$g_{mcrit} = (2 \times \Pi \times f_{HSE})^2 \times R_m(2Co + C)^2$$

Table 50. TS characteristics (continued)

Symbol	Parameter	Min	Typ	Max.	Unit
T_{START}(3)	Temperature sensor startup time	-	-	10(2)	µs
T_{S_TEMP}	ADC sampling time when reading the temperature sensor	-	5	10(2)	

1. Tested in production at V_{DD} = 3 V ±10 mV. The 8 LSB of the V_{125} ADC conversion result are stored in the TS_Factory_CONV_V125 byte.
2. Guaranteed by design.
3. Defined for ADC output reaching its final value ±1/2LSB.

9.3.12 Comparator characteristics

In the following table, data are guaranteed by design, not tested in production, unless otherwise specified.

Table 51. Comparator 1 characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	1.65	-	3.6(1)	V
T_A	Temperature range	-40	-	125(1)	°C
R_{400K}	R_{400K} value	300	400	500(1)	kΩ
R_{10K}	R_{10K} value	7.5	10	12.5(1)	
V_{IN}	Comparator input voltage range	0.6	-	V_{DDA}(1)	V
V_{REFINT}	Internal reference voltage	1.202	1.224	1.242	
t_{START}	Startup time after enable	-	7	10(1)	µs
t_d	Propagation delay(2)	-	3	10(1)	
V_{offset}	Comparator offset error	-	±3	±10(1)	mV
I_{CMP1}	Consumption(3)	-	160	260(1)	nA

1. Guaranteed by characterization results.
2. The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.
3. Comparator consumption only. Internal reference voltage not included.

9.3.15 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms to the ANSI/ESDA/JEDEC JS-001, JESD22-A115 and ANSI/ESD S5.3.1.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 61000 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 61. EMS data

Symbol	Parameter	Conditions		Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU} = 16 MHz, conforms to IEC 61000		3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU} = 16 MHz, conforms to IEC 61000	Using HSI	4A
			Using HSE	2B

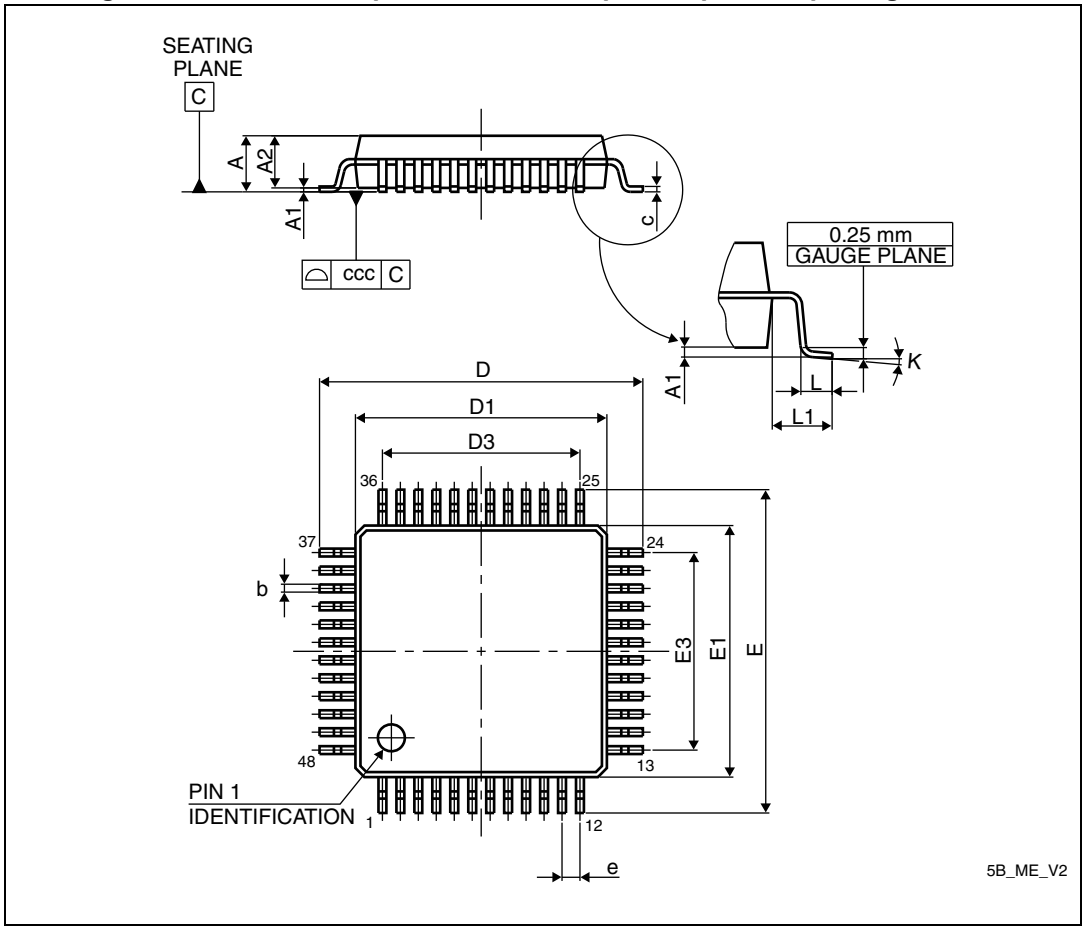
10 Package information

10.1 ECOPACK

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

10.2 LQFP48 package information

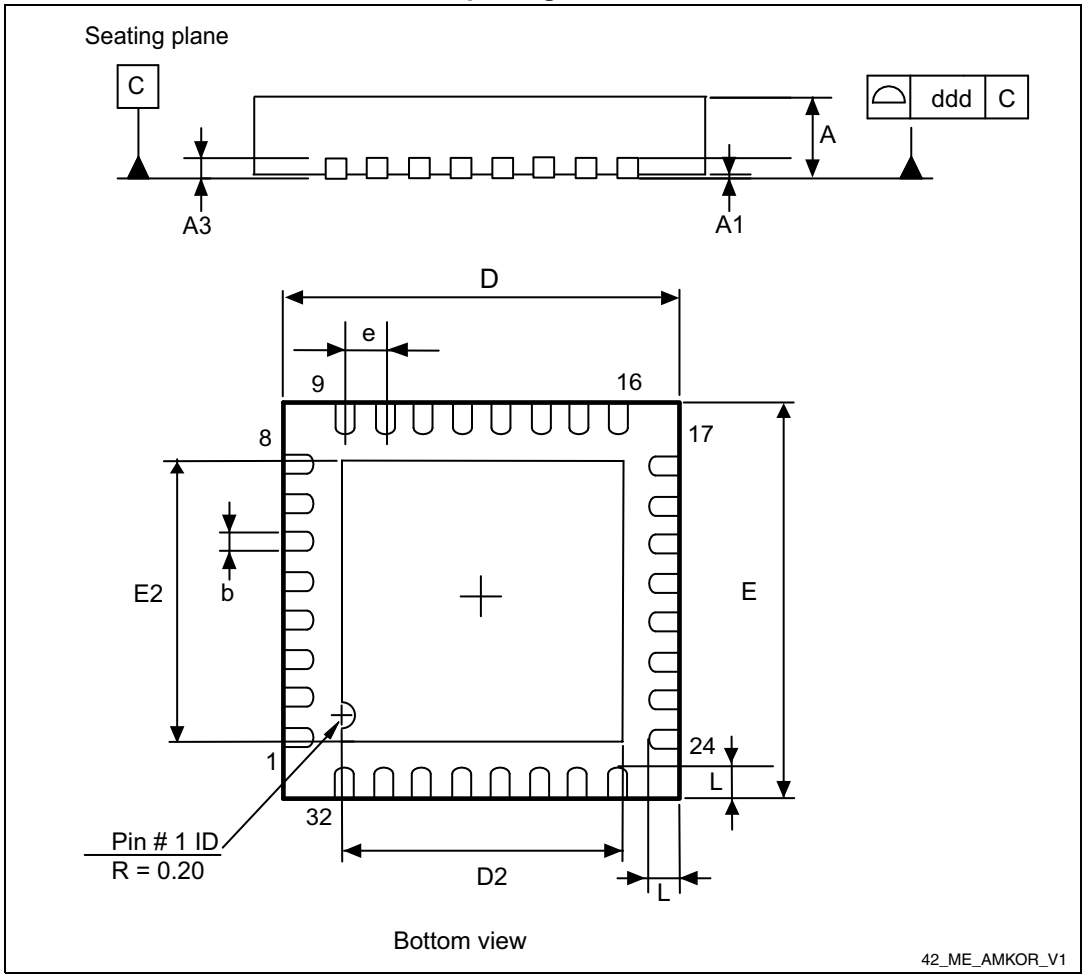
Figure 41. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

10.4 VFQFPN32 package information

Figure 47. VFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package outline



1. Drawing is not to scale.
2. There is an exposed die pad on the underside of the VQFPN package. It is recommended to connect and solder this backside pad to the PCB ground.

Table 67. VFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.800	0.900	1.000	0.0315	0.0354	0.0394
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.200	-	-	0.0079	-
b	0.180	0.250	0.300	0.0071	0.0098	0.0118
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D2	3.500	3.600	3.700	0.1378	0.1417	0.1457
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E2	3.500	3.600	3.700	0.1378	0.1417	0.1457
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

12 Revision history

Table 69. Document revision history

Date	Revision	Changes
04-Jan-2012	1	Initial release
20-Dec-2012	2	Added consumption values when run from Flash or from RAM. Added 8k Flash devices STM8AL3138 and STM8AL3136 to *Table 1: Device summary*, *Table 2: Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x low-power device features and peripheral counts*. and *Figure 50: Medium-density STM8AL313x/4x/6x and STM8AL3L4x/6x ordering information scheme*. Added footnotes stating that power consumption has not been tested to *Table 21* and *Table 22* for HSE, and to *Table 23* and *Table 24* for LSE. Updated max LSI amperage values in *Table 23* and *Table 24*. Replaced *Table 38: Flash program memory* and *Table 39: Data memory*. Added a production test footnote to *Table 50: TS characteristics*. Updated voltage values in *Table 50: TS characteristics*, and current values in *Table 51: Comparator 1 characteristics* and *Table 52: Comparator 2 characteristics*. Removed *Figure 13: Typ. $I_{DD(LPR)}$ vs. V_{DD} (LSI clock source)* and *Figure 14: Typ. $I_{DD(LPW)}$ vs. V_{DD} (LSI clock source)*.
03-Jun-2013	3	Updated ‘Qualification conforms’ bullet on cover page. Updated ‘TS_Factory_CONV’ in *Figure 9: Memory map* Removed ‘rev G’ in *Table 18: Operating lifetime (OLF)* Ratings Replaced 0.40 by 0.38 in *Table 22: Total current consumption in Wait mode* ‘code executed from Flash’ fcpu = 125 kHz Updated footnote (3) in *Table 23: Total current consumption and timing in low-power run mode at VDD = 1.65 V to 3.6 V*, *Table 24: Total current consumption in low-power wait mode at VDD = 1.65 V to 3.6 V* and *Table 27: Total current consumption and timing in Halt mode at VDD = 1.65 to 3.6 V* Updated footnote (2) in *Table 26: Typical current consumption in Active-halt mode, RTC clocked by LSE external crystal* Updated max ILEAK_HSE in *Table 30: HSE external clock characteristics* and *Table 31: LSE external clock characteristics* Updated ACC_{HSI} in *Table 34: HSI oscillator characteristics* Updated tprog max *Table 38: Flash program memory* Updated $STAB_{VREFINT}$ in *Table 49: Reference voltage characteristics* Updated ‘TS_Factory_CONV’ in *Table 50: TS characteristics* footnote. Updated ‘tconv’ and ‘title’ in *Table 56: ADC1 characteristics* Updated title in *Table 57: ADC1 accuracy with VDDA = 2.5 V to 3.3 V* Updated *Table 64: Electrical sensitivities*
14-Jun-2013	4	Updated max LSI measures in *Table 23: Total current consumption and timing in low-power run mode at VDD = 1.65 V to 3.6 V* and *Table 24: Total current consumption in low-power wait mode at VDD = 1.65 V to 3.6 V*